

GSMBT2907A

PNP EPITAXIAL PLANAR TRANSISTOR

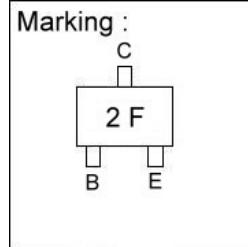
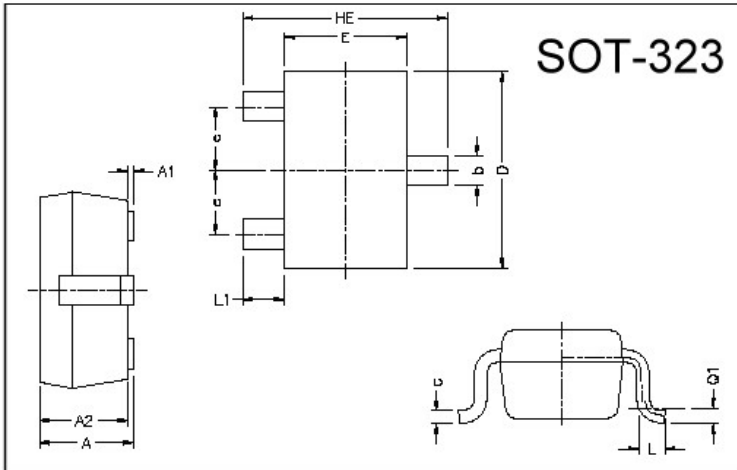
Description

The GSMBT2907A is designed for general purpose amplifier and high speed, medium-power switching applications.

Features

- Low collector saturation voltage
- High speed switching
- For complementary use with NPN type GSMBT2222A

Package Dimensions



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	0.80	1.10	L1	0.42 REF.	
A1	0	0.10	L	0.15	0.35
A2	0.80	1.00	b	0.25	0.40
D	1.80	2.20	c	0.10	0.25
E	1.15	1.35	e	0.65 REF.	
HE	1.80	2.40	Q1	0.15 BSC.	

Absolute Maximum Ratings at Ta = 25°C

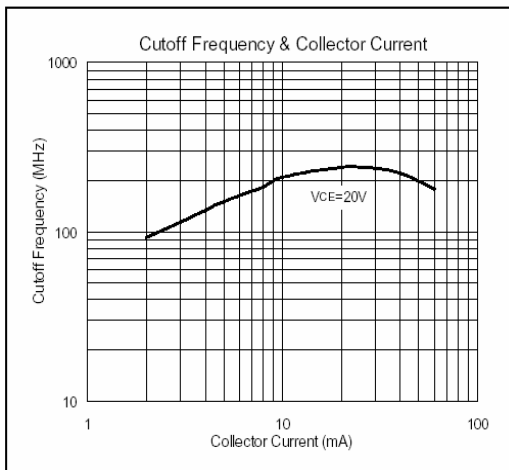
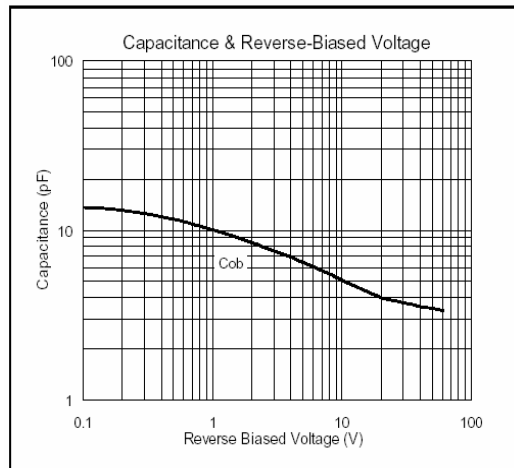
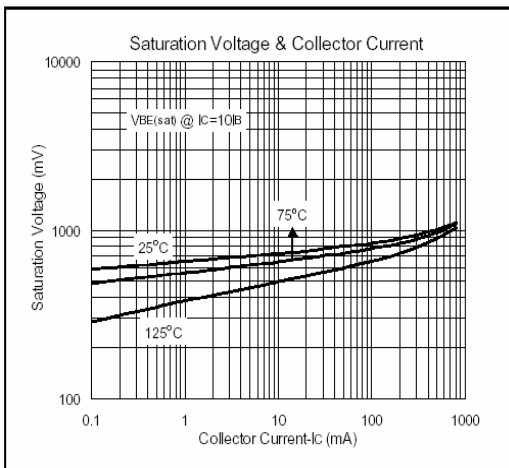
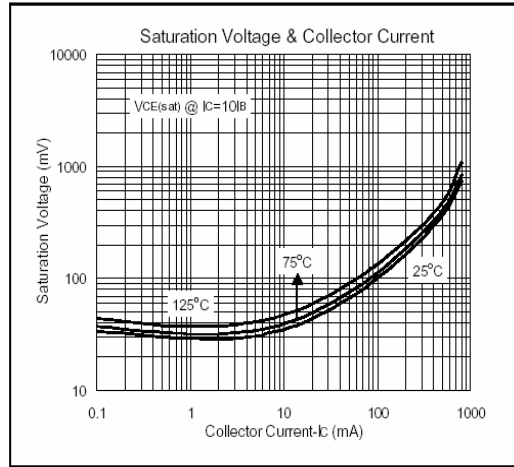
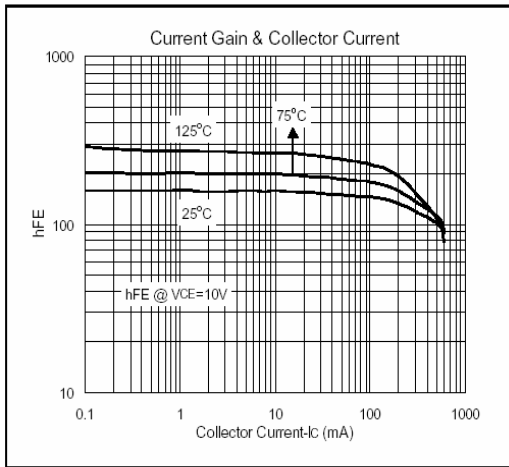
Parameter	Symbol	Ratings	Unit
Junction Temperature	T _j	+150	°C
Storage Temperature	T _{stg}	-55 ~ +150	°C
Collector to Base Voltage at Ta=25°C	V _{CBO}	-60	V
Collector to Emitter Voltage at Ta=25°C	V _{CEO}	-60	V
Emitter to Base Voltage at Ta=25°C	V _{EBO}	-5	V
Collector Current at Ta=25°C	I _C	-600	mA
Total Power Dissipation at Ta=25°C	P _D	225	mW

Characteristics at Ta = 25°C

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
V _{CBO}	-60	-	-	V	I _C =-10uA
V _{CEO}	-60	-	-	V	I _C =-10mA
V _{EBO}	-5	-	-	V	I _E =-10uA
I _{CBO}	-	-	-10	nA	V _{CE} =-50V
I _{CEX}	-	-	-50	nA	V _{CE} =-30V, V _{BE} =-0.5V
*V _{CE(sat)1}	-	-0.2	-0.4	V	I _C =-150mA, I _B =-15mA
*V _{CE(sat)2}	-	-0.5	-1.6	V	I _C =-500mA, I _B =-50mA
*V _{BE(sat)1}	-	-	-1.3	mV	I _C =-150mA, I _B =-15mA
*V _{BE(sat)2}	-	-	-2.6	V	I _C =-500mA, I _B =-50mA
*h _{FE1}	75	-	-		V _{CE} =-10V, I _C =-0.1mA
*h _{FE2}	100	-	-		V _{CE} =-10V, I _C =-1mA
*h _{FE3}	100	-	-		V _{CE} =-10V, I _C =-10mA
*h _{FE4}	100	180	300		V _{CE} =-10V, I _C =-150mA
*h _{FE5}	50	-	-		V _{CE} =-10V, I _C =-500mA
f _T	200	-	-	MHz	V _{CE} =-20V, I _C =-50mA, f=100MHz
C _{ob}	-	-	8.0	pF	V _{CE} =-10V, f=1MHz

* Pulse Test: Pulse Width ≤ 380μs, Duty Cycle ≤ 2%

Characteristics Curve



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